



ESD



TVS



TSS



MOV



GDT



PLED

BSS131-MS
Product specification

General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDS(ON)	ID
240V	7Ω	0.12A

Features

- 240V, 0.12A, RDS(ON) =7Ω@VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting

Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 SOT-23		

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	240	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (TA=25°C)	0.12	A
	Drain Current - Continuous (TA=70°C)	0.09	A
I _{DM}	Drain Current - Pulsed ¹	0.4	A
P _D	Power Dissipation (TA=25°C)	1.25	W
	Power Dissipation - Derate above 25°C	0.4	mW/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	80	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	240	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =100V, V _{GS} =0V, T _J =75°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±10	nA

On Characteristics

R _{DSON}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =0.1A	---	7.0	14	Ω
		V _{GS} =4.5V, I _D =0.1A	---	9.0	20	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.8	1.4	1.8	V
g _f	Forward Transconductance	V _{DS} =10V, I _D =0.08A	---	0.14	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{2,3}	V _{DS} =190V, V _{GS} =10V, I _D =0.1	---	0.2	---	nC
Q _{gs}	Gate-Source Charge ^{2,3}		---	0.18	---	
Q _{gd}	Gate-Drain Charge ^{2,3}		---	0.8	---	
T _{d(on)}	Turn-On Delay Time ^{2,3}	V _{DD} =120V, V _{GS} =10V, R _G =6 I _D =0.1A	---	3.5	---	ns
T _r	Rise Time ^{2,3}		---	3.2	---	
T _{d(off)}	Turn-Off Delay Time ^{2,3}		---	14	---	
T _f	Fall Time ^{2,3}		---	65	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	70	---	pF
C _{oss}	Output Capacitance		---	7.5	---	
C _{rss}	Reverse Transfer Capacitance		---	3.0	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	0.12	A
I _{SM}	Pulsed Source Current		---	---	0.24	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _s =0.1A, T _J =25°C	---	---	1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width \leq 300us, duty cycle \leq 2%.
3. Essentially independent of operating temperature.

Figure 1. Output Characteristics

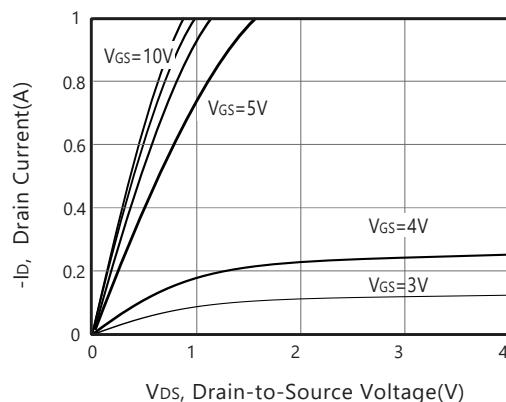


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

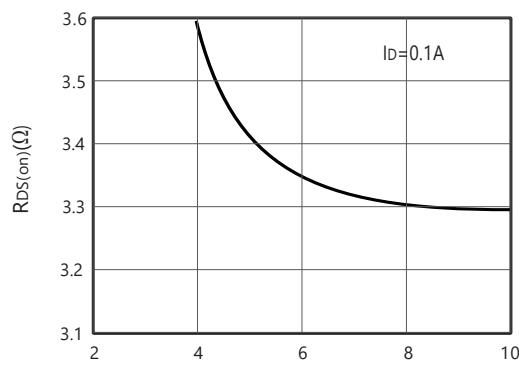


Figure 5. Gate Threshold Variation with Temperature

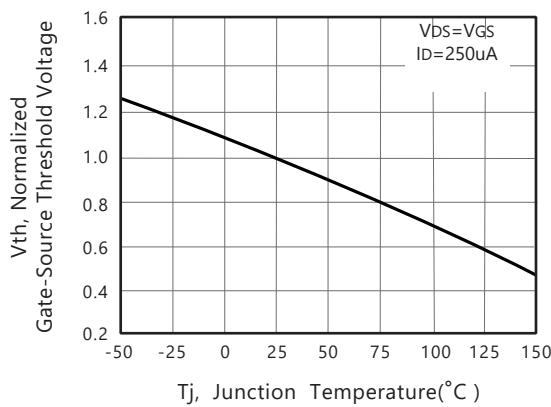


Figure 2. Body Diode Forward Voltage Variation with Source Current

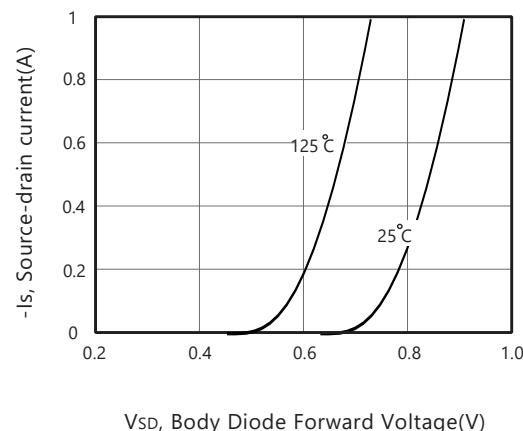


Figure 4. On-Resistance Variation with Drain Current and Temperature

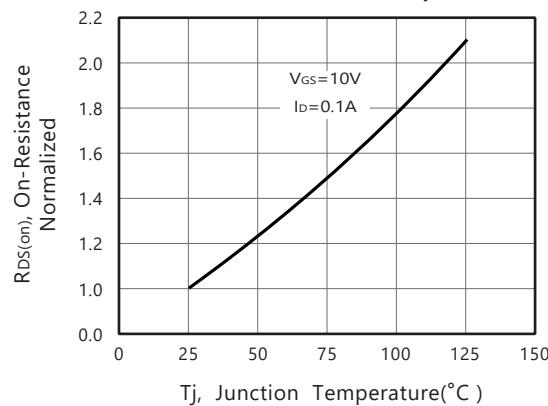


Figure 6. Gate Charge

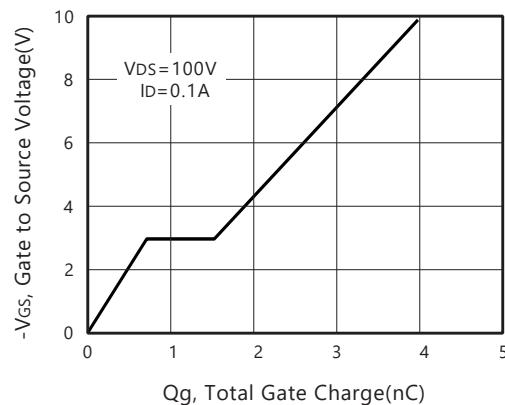


Figure 7. Capacitance

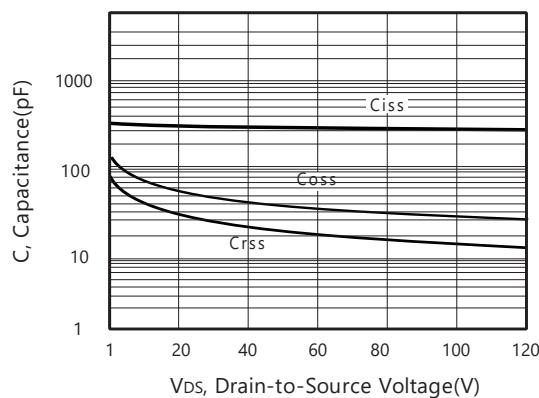


Figure 8. Maximum Safe Operating Area

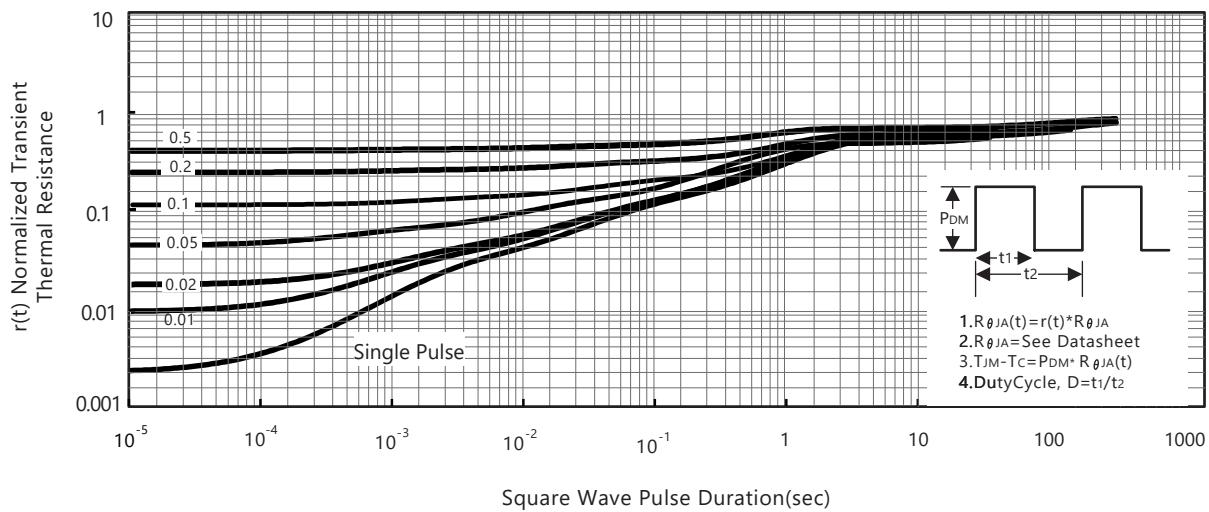
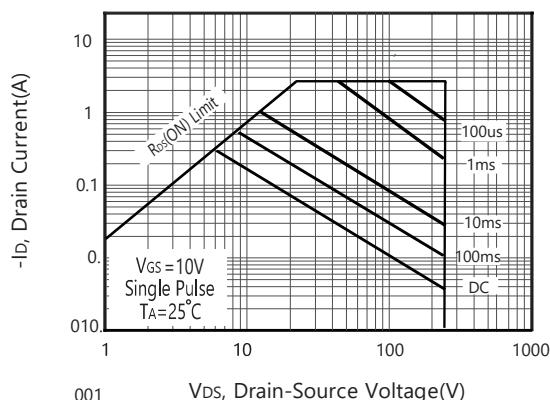
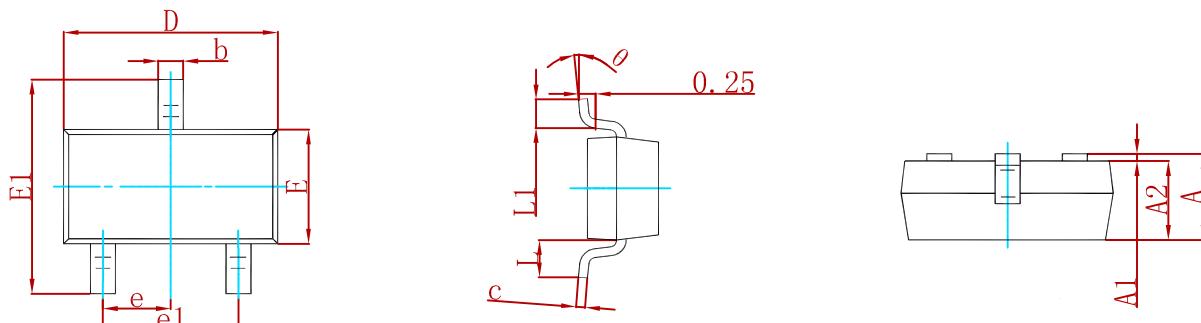
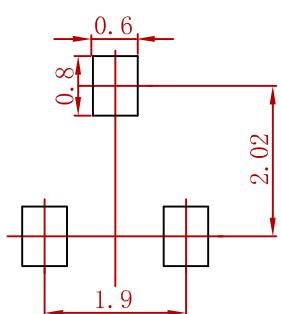


Figure 9. Normalized Thermal Transient Impedance Curve

PACKAGE MECHANICAL DATA


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BSS131-MS	SOT-23	3000

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